


Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2501	SERIAL NO. 10/769,149
		APPLICANT: Cem Basceri et al.	
		FILING DATE January 30, 2004	GROUP ART UNIT 1762

U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	6,566,147 B2	05/2003	Basceri et al.			
	AB	4,261,698	04/1981	Carr et al.			
	AC	4,691,662	09/1987	Roppel et al.			
	AD	5,270,241	12/1993	Dennison et al.			
	AE	5,312,783	05/1994	Takasaki et al.			
	AF	5,392,189	02/1995	Fazan et al.			
	AG	5,395,771	03/1995	Nakato			
	AH	5,468,687	11/1995	Carl et al.			
EF	AJ	5,261,961	11/1993	Takasu et al.			

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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
EF	AJ	0 030 798 A1	06/1981	EPO (Hughes Aircraft Company)			X	
EF	AK	GB 2 194 555 A	03/1988	UK (Nippon T & T Corporation)			X	
	AL	0 306 069 A2	03/1989	EPO (N.V. Phillips)			X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EF	AM	Stemmer et al., <i>Accommodation of nonstoichiometry in (100) fiber-textured (Ba_xSr_{1-x})Ti_{1-y}O_{3+z} thin films grown by chemical vapor deposition</i> , 74 APPL. PHYS. LETT., No. 17, pp. 2432-2434 (26 April 1999).
EF	AN	Streiffer et al., <i>Ferroelectricity in thin films: The dielectric response of fiber-textured (Ba_xSr_{1-x})Ti_{1-y}O_{3+z} thin films grown by chemical vapor deposition</i> , 86 J. APPL. PHYS. No. 8, pp. 4565-4575 (15 October 1999).

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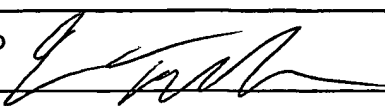
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Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	5,614,018	03/1997	Azuma et al.			
	AB	5,656,329	08/1997	Hampden-Smith			
	AC	5,663,089	09/1997	Tomozawa et al.			
	AD	5,702,562	12/1997	Wakahara			
	AE	5,719,417	02/1998	Roeder et al.			
	AF	5,723,361	03/1998	Azuma et al.			
	AG	5,736,759	04/1998	Haushalter			
EF	AH	5,525,156	06/1996	Manada et al.			
	AI						

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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
EF	AJ	0 388 957 A2	09/1990	EPO (NEC Corporation)			X	
	AK	08-060347	03/1996	Japan (Fujitsu Ltd)			X	
	AL	EP 0 810 666 A1	12/1997	EPO (Oki Electric)			X	
	AM	JP2000091333 A	03/2000	Japan (Fujitsu Ltd)			X	
	AN	WO 01/16395 A1	03/2001	WIPO (Micron Technology)			X	
	AO	JP2250970	10/1990	Japan (NEC Corp.)			Abstract	
EF	AP	04-024922	01/1992	Abstract:: Japan (Mitsubishi)			Abstract	

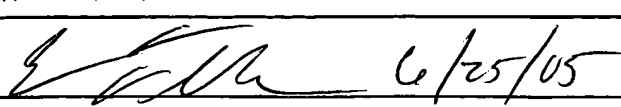
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)	
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EF	AA	6,325,017 B1	12/2001	DeBoer et al.			
	AB	5,976,990	11/1999	Mercaldi et al.			
	AC	5,989,927	11/1999	Yamonobe			
	AD	6,101,085	08/2000	Kawahara et al.			
	AE	6,215,650	04/2001	Gnade et al.			
	AF	6,258,654	07/2001	Gocho			
EF	AG	6,287,935 B1	09/2001	Coursey			
	AH						

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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
EF	AJ	EP 0 892 426 A2	01/1999	EPO (Ramtron International)			X	
	AJ	0 474 140 A1	30.08.91	EPO (Kamiyama)			X	
	AK	0 835 950 A1	13.10.97	EPO (Shinozaka et al.)			X	
	AL	04-115533	04/1992	Abstract: Japan (OKI Electric)			Abstract	
EF	AM	04-180566	06/1992	Japan (Matsushita Electric)			Abstract	

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EF	AO	Aoyama et al., <i>Leakage Current Mechanism of Amorphous and Polycrystalline Ta₂O₅ Films Grown by Chemical Vapor Deposition</i> , 143 J. ELECTROCHEM SOC., No. 3, pp 977-983 (March 1996).
EF	AP	Valiev et al., <i>Plastic deformation of alloys with submicron-grained structure</i> , MATERIALS SCIENCE AND ENGINEERING, A137, pp. 35-40 (1991).
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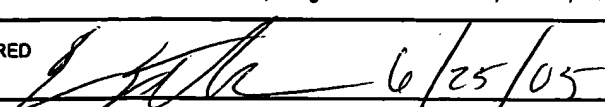
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EF	AA	4,105,810	08/1978	Yamazaki et al.			
	AB	5,006,363	04/1991	Fujii et al.			
	AC	5,164,363	11/1992	Eguchi et al.			
	AD	5,183,510	02/1993	Kimura			
	AE	5,254,505	10/1993	Kamiyama			
	AF	5,256,455	10/1993	Numasawa			
	AG	5,459,635	10/1995	Tomozawa et al.			
	AH	5,470,398	11/1995	Takashi et al.			
EF	AI	5,596,214	01/1997	Endo			

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Examiner's Initials	Class	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
EF	AI	00 474 140 A1	08/1991	EPO (NEC Corp.)				
EF	AK	0 855 735 A2	07/1998	EPO (Applied Materials)				
EF	AL	98/39497	09/1998	WIPO (Sec. of State for Defence/GB)				

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EF	AM	Tomoko Tsuyama Arai et al., <i>Preparation of SrTiO₃ Films on 8-Inch Wafers by Chemical Vapor Deposition</i> , JPN. J. APPL. PHYS., Vol. 35 (1996) pp. 4875-4879
EF	AN	DISSERTATION: Cem Basceri, <i>Electrical and Dielectric Properties of (Ba,Sr)TiO₃ Thin Film Capacitors for Ultra-High Density Dynamic Random Access Memories</i> , Dept. of Mat. Sci. & Eng., NC State Univ. (1997).
EF	AO	Cem Basceri et al., <i>The dielectric response as a function of temperature and film thickness of fiber-textured (Ba,Sr)TiO₃ thin films grown by chemical ...</i> , J. Appl. Phys., Vol. 82, No. 5 (1 Sept. 1997) pp. 2497-2504.
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U.S. PATENT DOCUMENTS							
Examiner's Initials	Class	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
EF	AA	5,618,761	04/1997	Eguchi et al.			
	AB	5,635,741	06/1997	Tsu et al.			
	AC	5,711,816	01/1998	Kirlin et al.			
	AD	5,731,948	03/1998	Yializis et al.			
	AE	5,776,254	07/1998	Yuuki et al.			
	AF	5,783,253	07/1998	Roh			
	AG	5,798,903	08/1998	Dhote et al.			
	AH	5,834,060	11/1998	Kawahara et al.			
EF	AI	5,909,043	06/1999	Summerfelt			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
EF	AJ	0 957 522 A2	11/1999	EPO (Matsushita Elec. Ind.)			
EF	AK	99/64645	12/1999	WIPO (Applied Materials)			
EF	AL						
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EF	AM		PRESENTATION: Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD</i>				
			<i>Ba_xSr_{1-x}TiO₃</i> , MRS Fall Meeting, Advanced Technology Materials (Dec. 1, 1994) pp. 1-21.				
EF	AN		Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> , CVD Technologies for Inter-Level				
			Dielectrics and Interconnects Symposium, SEMICONWEST (July 12, 1995) 2 pages.				
EF	AO		ABSTRACT: Y. C. Choi et al., <i>Improvements of the Properties of Chemical-Vapor-Deposited (Ba,Sr)TiO₃</i>				
			<i>Films Through Use of a Seed Layer</i> , JPN. J. APPL. PHYS., Vol. 1, Pt. 1, No. 11 (1997) pp. 6824-6828.				
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U.S. PATENT DOCUMENTS							
Examiner's Initials	Class	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	5,972,430	10/1999	DiMeo, Jr. et al.			
	AB	6,025,222	02/2000	Kimura et al.			
	AC	6,037,205	03/2000	Huh et al.			
	AD	6,043,526	03/2000	Ochiai			
	AE	6,046,345	04/2000	Kadokura et al.			
	AF	6,078,492	08/2000	Huang et al.			
	AG	6,090,443	07/2000	Easteo			
	AH	6,126,753	10/2000	Shinriki et al.			
EF	AI	6,127,218	10/2000	Kang			
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EF	AM		ABSTRACT: Chung Ming Chu et al., <i>Electrical Properties and crystal structure of (Ba,Sr)TiO₃ films</i>				
			Prepared at low temperatures on a ..., APPLIED PHYSICS LETTERS, Vol. 70, No. 2 (1997) pp. 249-251.				
EF	AN		ABSTRACT: Kazuhiro Eguchi et al., <i>Chemical vapor deposition of (Ba,Sr)TiO₃ thin films for application in a</i>				
			gigabit scale dynamic ..., INTEGRATED FERROELECTRICS, Vol. 14, Nos. 1-4, Pt. 1 (1997) pp. 33-42.				
EF	AO		ABSTRACT: Q. X. Jia et al., <i>Structural and dielectric properties of Ba/sub 0.5/Sr/sub 0.5/TiO₃ thin films</i>				
			with an epi-RuO ₃ /sub 2/ bottom electrode, Integrated Ferroelectrics, Vol. 19, Nos. 1-4 (1998) pp. 111-119.				
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EF	AA	6,143,679	11/2000	Nagasawa					
	AB	6,146,907	11/2000	Xiang et al.					
	AC	6,150,684	11/2000	Sone					
	AD	6,153,898	11/2000	Watanabe					
	AE	6,156,638	12/2000	Agarwal et al.					
	AF	6,165,834	12/2000	Agarwal et al.					
	AG	6,211,096 B1	04/2001	Allman					
	AH	6,236,076 B1	05/2001	Arita et al.					
EF	AI	6,238,734 B1	05/2001	Senzaki et al.					
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							Yes	No	
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EF	AM		Takaaki Kawahara et al., (Ba, Sr)TiO ₃ Films Prepared by Liquid Source Chemical Vapor Deposition on Ru						
			Electrodes, Jpn. J. Appl. Phys., Vol. 35, Pt. 1, No. 9B (1996) pp. 4880-4883.						
EF	AN		Rajesh Khamankar et al., A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for						
			ULSI DRAM Applications, Microelectronic Res. Center, Univ. of TX at Austin, TX (Undated) 2 pages.						
EF	AO		ABSTRACT: Yong Tae Kim et al., Advantages of RuO ₂ /sub x/ bottom electrode in the dielectric and leakage						
			characteristics of ..., JPN. J. APPL. PHYS., Vol. 35, Pt. 1, No. 12A (1996) pp. 6153-6156.						
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	AB	6,258,170 B1	07/2001	Somekh					
	AC	6,277,436 B1	08/2001	Stauf et al.					
	AD	6,285,051 B1	09/2001	Ueda et al.					
	AE	6,323,057 B1	11/2001	Sone					
	AF	6,335,049 B1	01/2002	Basceri					
	AG	6,335,302 B1	01/2002	Satoh					
	AH	6,337,496 B2	01/2002	Jung					
EF	AI	6,338,970 B1	01/2002	Suh					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
EF	AM		T. W. Kim et al., <i>Structural and electrical properties of BaTiO₃ grown on p-InP (100) by low-pressure metal-organic chemical vapor deposition ...</i> , APPL. PHYS. LETT., Vol. 65, No. 15 (10 Oct. 1994) pp. 1955-1957.						
EF	AN		ABSTRACT: S. H. Paek et al., <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron ...</i> , Ferroelectric Thin Films V. Symposium, San Francisco, CA (April 7, 1995) pp. 33-38.						
EF	AO		ABSTRACT: N. Takeuchi et al., <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba /sub 0.99/Sr sub ...</i> , NIPPON SERAMIKKUSU KYOKAI GAKUJUTSU RONBUNSHI, Vol. 98, No. 8 (1990) pp. 836-839.						
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EF	AA	6,362,068 B1	03/2002	Summerfelt				
	AB	6,372,686 B1	04/2002	Golden				
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EF	AM		ABSTRACT: H. Yamaguchi et al., <i>Reactive coevaporation synthesis and characterization of SrTiO/sub 3/ ...</i>					
			IEEE Internat'l Symposium on Applications of Ferroelectrics, Greenville, SC (08/02/1992) pp. 285-288.					
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			<i>SUB . SUB 5 Sr SUB 0 SUB . SUB 5)TiO ...</i> , APPL. PHYS. LETT., Vol. 64, No. 13 (1994) pp. 1644-1646.					
EF	AO		ABSTRACT: M. Yamamuka et al., <i>Thermal-Desorption Spectroscopy of (Ba, Sr)TiO3 Thin-Films Prepared by</i>					
			<i>Chemical-Vapor-Deposition</i> , JPN. J. OF APPL. PHYS., Vol. 35, Pt. 1, No. 2A (1996) pp. 729-735.					
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EP	AA	09/388,063	Agarwal et al.			08/1999	
	AB	09/580,733	Basceri			05/2000	
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	AD	09/776,217	Basceri			02/2001	
	AE	09/905,286	Basceri et al.			07/2001	
	AF	2002/0197793	12/2002	Dornfest et al.			
	AG	2003/0045006 A1	03/2003	Basceri			
EP	AH	2003/0017266 A1	01/2003	Basceri et al.			
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